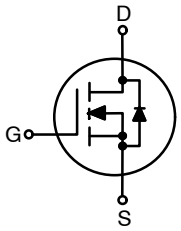
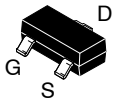
MOSFET – N-Channel, POWERTRENCH®, 1.8 V_{gs} Specified

20 V, 2 A, 70 mΩ

FDN327N





SOT-23/SUPERSOT™-23, 3 LEAD, 1.4x2.9
CASE 527AG

General Description

This 20 V N-Channel MOSFET uses **onsemi**'s high voltage POWERTRENCH process. It has been optimized for power management applications.

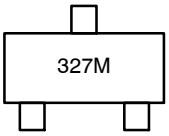
Features

- 2 A, 20 V
  - $R_{DS(on)}$ = 70 mΩ @ V_{GS} = 4.5 V
  - $R_{DS(on)}$ = 80 mΩ @ V_{GS} = 2.5 V
  - $R_{DS(on)}$ = 120 mΩ @ V_{GS} = 1.8 V
- Low Gate Charge (4.5 nC typical)
- Fast Switching Speed
- High Performance Trench Technology for Extremely Low $R_{DS(on)}$
- This Device is Pb-Free and Halogen Free

Applications

- Load Switch
- Battery Protection
- Power Management

MARKING DIAGRAM



327 = Specific Device Code
M = Assemble Operation Month

ORDERING INFORMATION

Device	Package	Shipping†
FDN327N	SOT-23-3 (Pb-Free/Halide Free)	3000 / Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ABSOLUTE MAXIMUM RATINGS

T_A = 25 °C unless otherwise noted.

Symbol	Parameter	Ratings	Unit
V_{DSS}	Drain-Source Voltage	20	V
V_{GSS}	Gate-Source Voltage	±8	V
I_D	Drain Current – Continuous (Note 1a)	2	A
	Drain Current – Pulsed	8	
P_D	Power Dissipation for Single Operation (Note 1a)	0.5	W
	Power Dissipation for Single Operation (Note 1b)	0.46	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	–55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Symbol	Parameter	Ratings	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	250	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	75	°C/W

ELECTRICAL CHARACTERISTICS T_A = 25 °C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 μA	20	–	–	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25 °C	–	12	–	mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 16 V, V_{GS} = 0 V	–	–	1	μA
I_{GSSF}	Gate-Body Leakage, Forward	V_{GS} = 8 V, V_{DS} = 0 V	–	–	100	nA
I_{GSSR}	Gate-Body Leakage, Reverse	V_{GS} = −8 V, V_{DS} = 0 V	–	–	−100	nA
ON CHARACTERISTICS (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 μA	0.4	0.7	1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25 °C	–	−3	–	mV/°C
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 4.5 V, I_D = 2.0 A	–	40	70	mΩ
		V_{GS} = 2.5 V, I_D = 1.9 A	–	49	80	
		V_{GS} = 1.8 V, I_D = 1.6 A	–	65	120	
		V_{GS} = 4.5 V, I_D = 2 A, T_J = 125 °C	–	55	103	
$I_{D(on)}$	On-State Drain Current	V_{GS} = 4.5 V, V_{DS} = 5 V	8	–	–	A
g_{FS}	Forward Transconductance	V_{DS} = 5 V, I_D = 2 A	–	11	–	S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{DS} = 10 V, V_{GS} = 0 V, f = 1.0 MHz	–	423	–	pF
C_{oss}	Output Capacitance		–	87	–	
C_{rss}	Reverse Transfer Capacitance		–	48	–	
SWITCHING CHARACTERISTICS (Note 2)						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 10 V, I_D = 1 A, V_{GS} = 4.5 V, R_{GEN} = 6 Ω	–	6	12	ns
t_r	Turn-On Rise Time		–	6.5	13	
$t_{d(off)}$	Turn-Off Delay Time		–	14	29	
t_f	Turn-Off Fall Time		–	2	4	
Q_g	Total Gate Charge	V_{DS} = 10 V, I_D = 2 A, V_{GS} = 4.5 V	–	4.5	6.3	nC
Q_{gs}	Gate-Source Charge		–	0.89	–	
Q_{gd}	Gate-Drain Charge		–	0.95	–	
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
I_S	Maximum Continuous Drain-Source Diode Forward Current		–	–	0.42	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 0.42 A (Note 2)	–	0.6	1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NOTES:

1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.

a) 250 °C/W when mounted on a 0.02 in^2 pad of 2 oz. copper.

b) 270 °C/W when mounted on a minimum pad.

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

TYPICAL CHARACTERISTICS

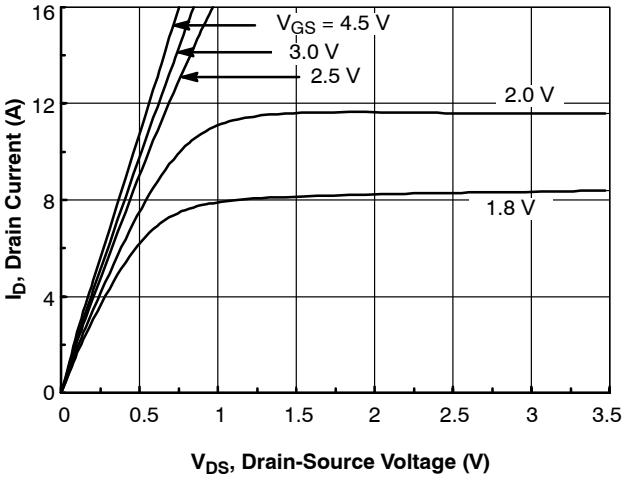


Figure 1. On-Region Characteristics

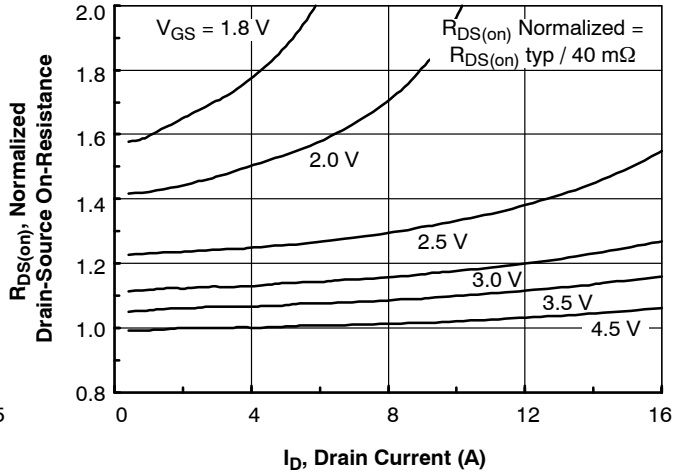


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage

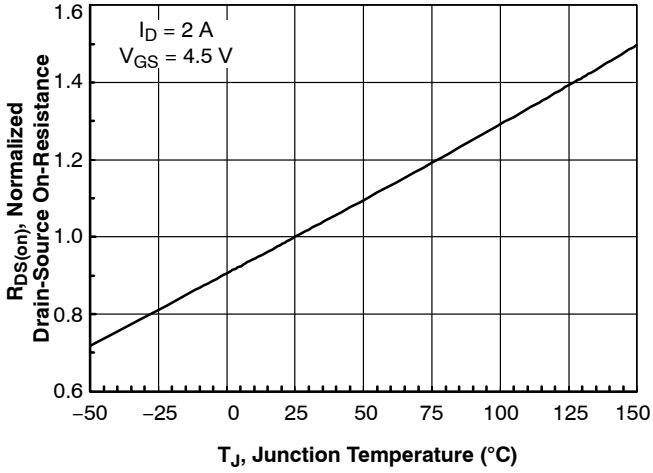


Figure 3. On-Resistance Variation with Temperature

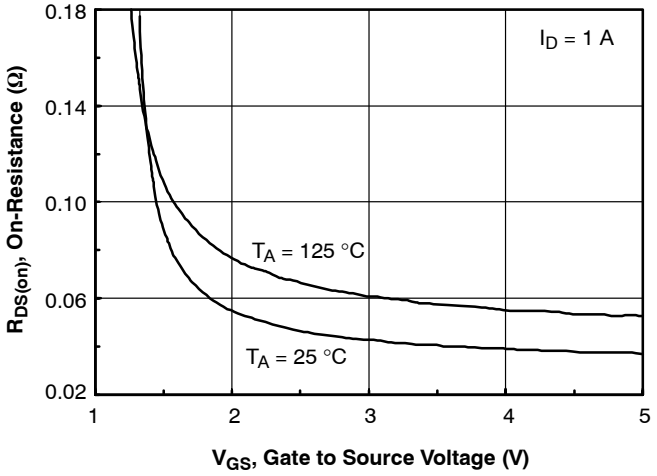


Figure 4. On-Resistance Variation with Gate-to-Source Voltage

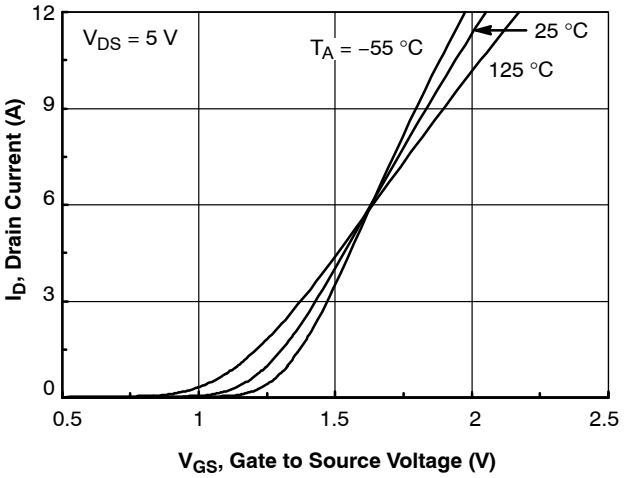


Figure 5. Transfer Characteristics

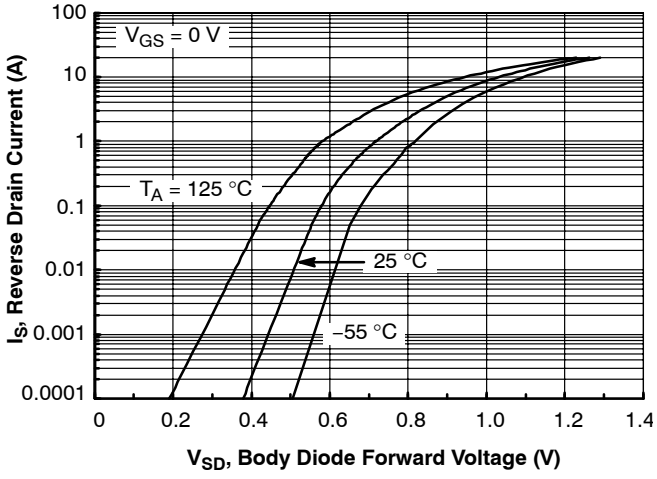


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

TYPICAL CHARACTERISTICS (continued)

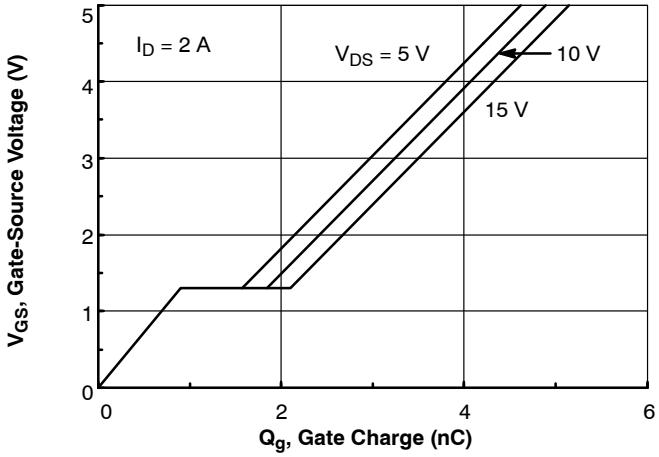


Figure 7. Gate Charge Characteristics

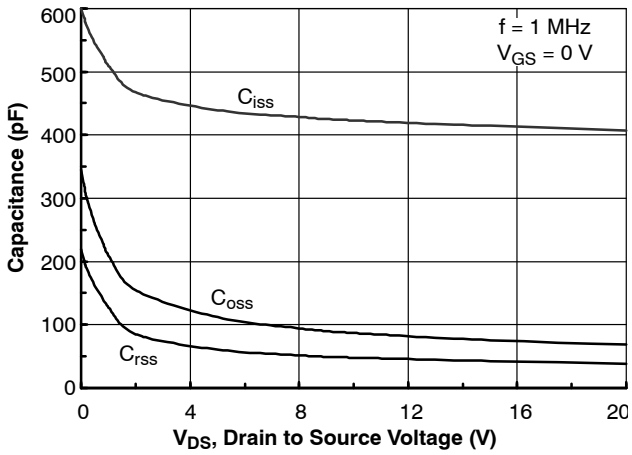


Figure 8. Capacitance Characteristics

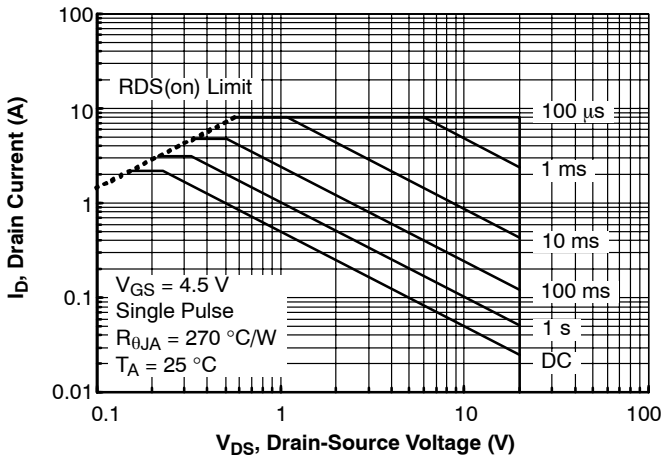


Figure 9. Maximum Safe Operating Area

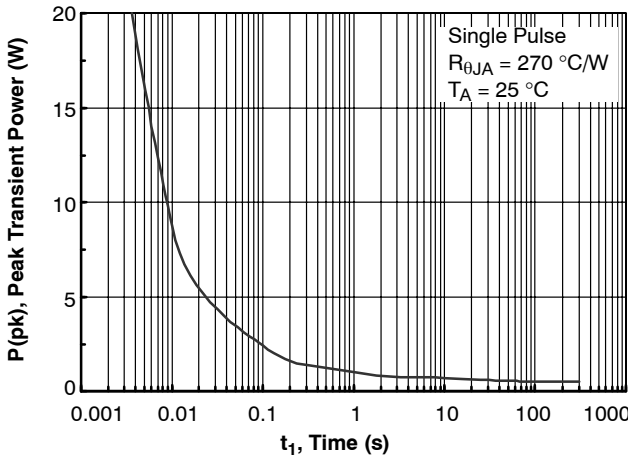


Figure 10. Single Pulse Maximum Power Dissipation

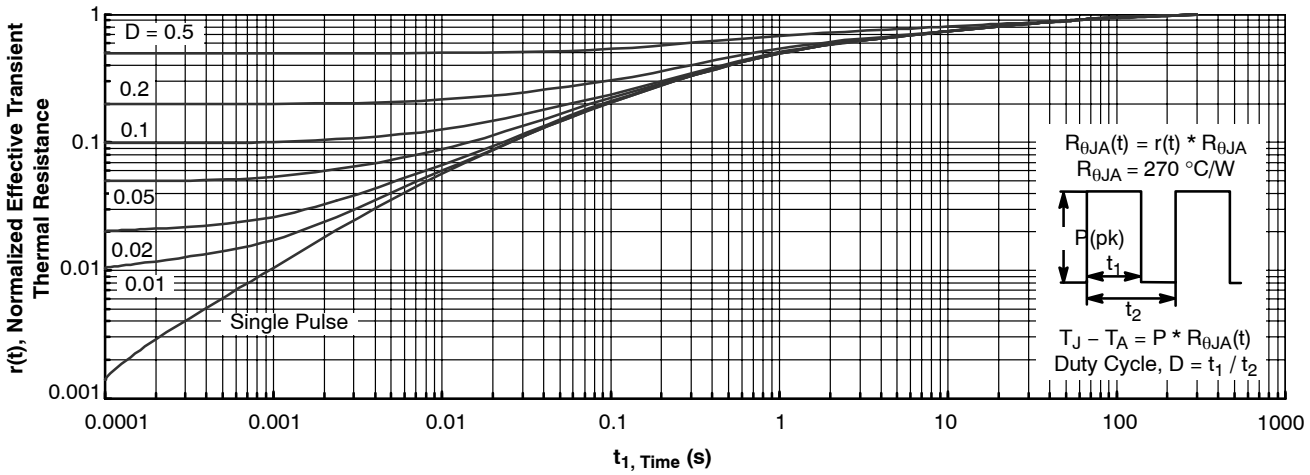


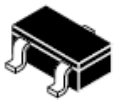
Figure 11. Transient Thermal Response Curve

Thermal characterization performed using the conditions described in Note 1b.
Transient thermal response will change depending on the circuit board design.

REVISION HISTORY

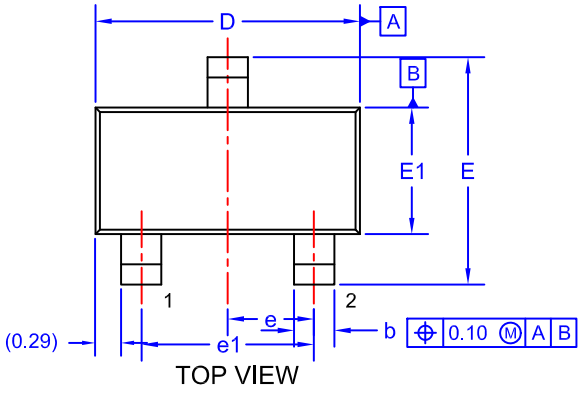
Revision	Description of Changes	Date
6	Comment "$R_{DS(on)}$ Normalized = $R_{DS(on)}$ typ / 40 mΩ" added in Figure 2.	11/14/2025

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.



SOT−23/SUPERSOT™ −23, 3 LEAD, 1.4x2.9
CASE 527AG
ISSUE A

DATE 09 DEC 2019

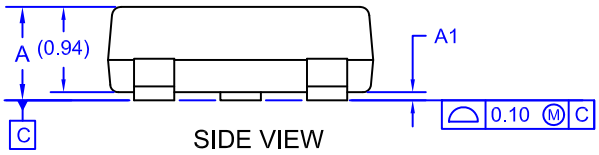


TOP VIEW

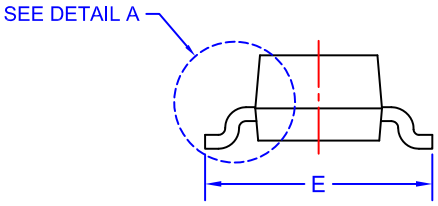
NOTES: UNLESS OTHERWISE SPECIFIED

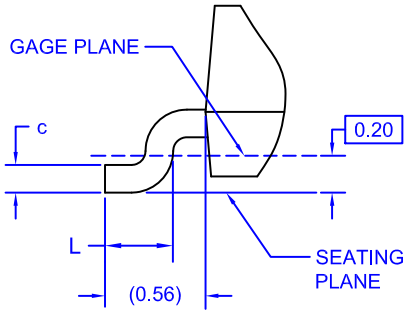
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. ALL DIMENSIONS ARE IN MILLIMETERS.
3. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.

DIM	MIN.	NOM.	MAX.
A	0.85	0.95	1.12
A1	0.00	0.05	0.10
b	0.370	0.435	0.508
c	0.085	0.150	0.180
D	2.80	2.92	3.04
E	2.31	2.51	2.71
E1	1.20	1.40	1.52
e	0.95 BSC		
e1	1.90 BSC		
L	0.33	0.38	0.43

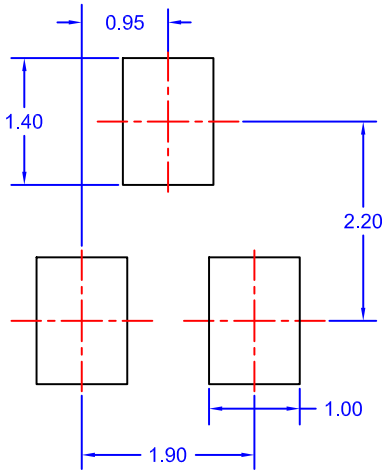


SIDE VIEW





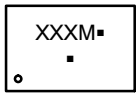
DETAIL A



LAND PATTERN RECOMMENDATION*

*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Month Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	**SOT−23/SUPERSOT−23, 3 LEAD, 1.4X2.9**	**PAGE 1 OF 1**

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